MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

MMDL914

Product specification

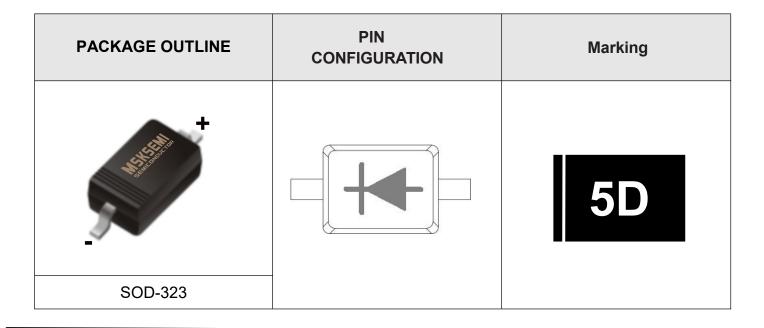




FEATURES

High Voltage

Reference News



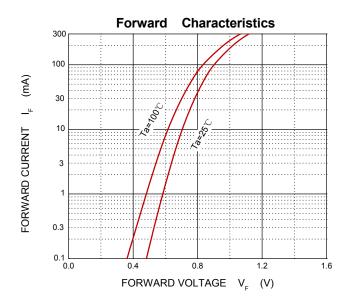
MAXIMUM RATINGS (Ta=25 $^{\circ}$ C unless otherwise noted)

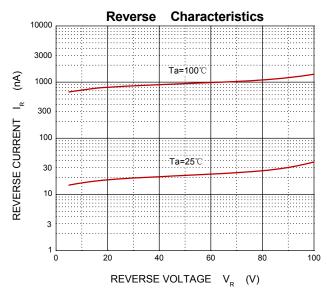
Symbol	Parameter	Value	Unit	
V _{RRM}	Maximum Repetitive Reverse Voltage	100	V	
lo	Forward Current	0.2	۸	
I _{FSM}	Non-repetitive Peak Forward Surge Current @t= 8.3ms	2	A	
P _D	Power Dissipation	200	mW	
Reja	Thermal Resistance from Junction to Ambient	500	°C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$	

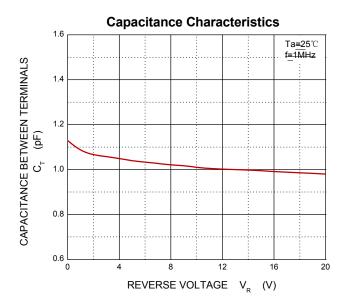
ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified)

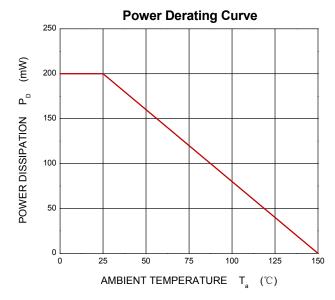
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Reverse voltage	V _(BR)	l _R =100μA	100			V
Reverse current	L	V _R =20V			25	nA
	l _R	V _R =75V			5	μA
Forward voltage	V _F	l⊧=10mA			1	V
Total capacitance	C _{tot}	V _R =0V,f=1MHz			4	pF
Reverse recovery time	t _{rr}	$I_F = I_R = 10$ mA, $I_{rr} = 0.1 \times I_R$, $R_L = 100$ Ω			4	ns





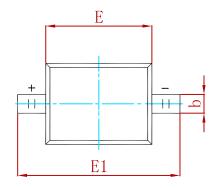


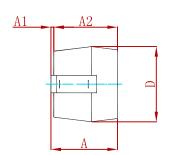


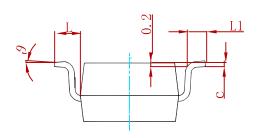




PACKAGE MECHANICAL DATA

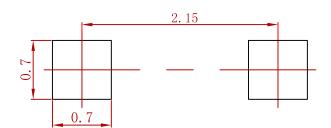






Occurred to a 1	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
Α		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
С	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMDL914	SOD-323	3000



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